

NTP75N03L09, NTB75N03L09

Power MOSFET

75 Amps, 30 Volts, N-Channel TO-220 and D²PAK

This Logic Level Vertical Power MOSFET is a general purpose part that provides the “best of design” available today in a low cost power package. Avalanche energy issues make this part an ideal design in. The drain-to-source diode has a ideal fast but soft recovery.

Features

- Pb-Free Packages are Available
- Ultra-Low $R_{DS(on)}$, Single Base, Advanced Technology
- SPICE Parameters Available
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and $V_{DS(on)}$ Specified at Elevated Temperatures
- High Avalanche Energy Specified
- ESD JEDAC Rated HBM Class 1, MM Class B, CDM Class 0

Typical Applications

- Power Supplies
- Inductive Loads
- PWM Motor Controls
- Replaces MTP75N03HDL and MTB75N03HDL in Many Applications

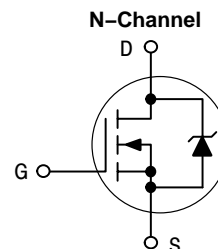


ON Semiconductor®

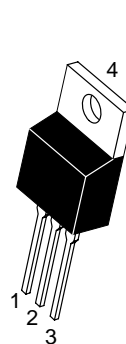
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75 AMPERES, 30 VOLTS

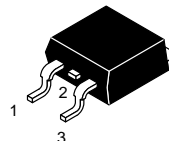
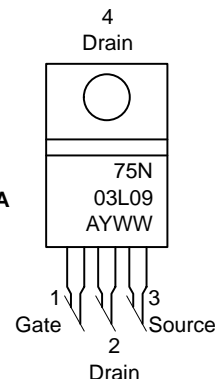
$R_{DS(on)} = 8\text{ m}\Omega$



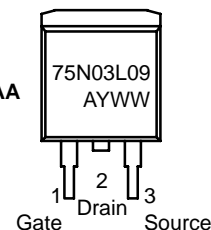
MARKING DIAGRAMS



**TO-220
CASE 221A
STYLE 5**



**D²PAK
CASE 418AA
STYLE 2**



75N03L09 = Device Code
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NTP75N03L09, NTB75N03L09

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	30	Vdc
Drain-to-Gate Voltage (R _{GS} = 10 MΩ)	V _{DGB}	30	Vdc
Gate-to-Source Voltage – Continuous	V _{GS}	±20	Vdc
Non-repetitive (tp ≤ 10 ms)	V _{GS}	±24	Vdc
Drain Current – Continuous @ T _C = 25°C – Continuous @ T _C = 100°C – Single Pulse (tp ≤ 10 μs)	I _D I _D I _{DM}	75 59 225	Adc Adc Apk
Total Power Dissipation @ T _C = 25°C Derate above 25°C Total Power Dissipation @ T _A = 25°C (Note 1)	P _D	125 1.0 2.5	W W/°C W
Operating and Storage Temperature Range	T _J and T _{stg}	–55 to 150	°C
Single Pulse Drain-to-Source Avalanche Energy – Starting T _J = 25°C (V _{DD} = 38 Vdc, V _{GS} = 10 Vdc, L = 1 mH, I _{L(pk)} = 55 A, V _{DS} = 40 Vdc)	E _{AS}	1500	mJ
Thermal Resistance – Junction-to-Case – Junction-to-Ambient – Junction-to-Ambient (Note 1)	R _{θJC} R _{θJA} R _{θJA}	1.0 62.5 50	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T _L	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. When surface mounted to an FR4 board using the minimum recommended pad size.

ORDERING INFORMATION

Device	Package	Shipping†
NTP75N03L09	TO-220	50 Units/Rail
NTP75N03L09G	TO-220 (Pb-Free)	50 Units/Rail
NTB75N03L09	D ² PAK	50 Units/Rail
NTB75N03L09G	D ² PAK (Pb-Free)	50 Units/Rail
NTB75N03L09T4	D ² PAK	800 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTP75N03L09, NTB75N03L09

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain–Source Breakdown Voltage (Note 2) ($V_{GS} = 0\text{ Vdc}$, $I_D = 250\text{ }\mu\text{Adc}$) Temperature Coefficient (Negative)	$V_{(BR)DSS}$	30	34 –57	– –	Vdc mV $^\circ\text{C}$
Zero Gate Voltage Drain Current ($V_{DS} = 30\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) ($V_{DS} = 30\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $T_J = 150^\circ\text{C}$)	I_{DSS}	– –	– –	1.0 10	μAdc
Gate–Body Leakage Current ($V_{GS} = \pm 20\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	–	–	± 100	nAdc

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage (Note 2) ($V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{Adc}$) Threshold Temperature Coefficient (Negative)	$V_{GS(th)}$	1.0 –	1.6 –6	2.0 –	Vdc mV $^\circ\text{C}$
Static Drain–to–Source On–Resistance (Note 2) ($V_{GS} = 5.0\text{ Vdc}$, $I_D = 37.5\text{ Adc}$)	$R_{DS(on)}$	–	6.5	8.0	m Ω
Static Drain–to–Source On Resistance (Note 2) ($V_{GS} = 10\text{ Vdc}$, $I_D = 75\text{ Adc}$) ($V_{GS} = 10\text{ Vdc}$, $I_D = 37.5\text{ Adc}$, $T_J = 125^\circ\text{C}$)	$V_{DS(on)}$	– –	0.52 0.35	0.68 0.50	Vdc
Forward Transconductance (Notes 2 & 4) ($V_{DS} = 3\text{ Vdc}$, $I_D = 20\text{ Adc}$)	g_{FS}	–	58	–	m Ω

DYNAMIC CHARACTERISTICS (Note 4)

Input Capacitance	$(V_{DS} = 25\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{iss}	–	4398	5635	pF
Output Capacitance		C_{oss}	–	1160	1894	
Transfer Capacitance		C_{rss}	–	317	430	

SWITCHING CHARACTERISTICS (Notes 3 & 4)

Turn–On Delay Time	$(V_{GS} = 5.0\text{ Vdc}$, $V_{DD} = 20\text{ Vdc}$, $I_D = 75\text{ Adc}$, $R_G = 4.7\text{ }\Omega$) (Note 2)	$t_{d(on)}$	–	16	30	ns
Rise Time		t_r	–	130	200	
Turn–Off Delay Time		$t_{d(off)}$	–	65	110	
Fall Time		t_f	–	105	175	
Gate Charge	$(V_{GS} = 5.0\text{ Vdc}$, $I_D = 75\text{ Adc}$, $V_{DS} = 24\text{ Vdc}$) (Note 2)	Q_T	–	57	75	nC
		Q_1	–	11	15	
		Q_2	–	34	50	

SOURCE–DRAIN DIODE CHARACTERISTICS

Forward On–Voltage	$(I_S = 75\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$) ($I_S = 75\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$, $T_J = 125^\circ\text{C}$) (Note 2)	V_{SD}	– –	1.19 1.09	1.25 –	Vdc
Reverse Recovery Time (Note 4)	$(I_S = 75\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$ $di_S/dt = 100\text{ A}/\mu\text{s}$) (Note 2)	t_{rr}	–	37	–	ns
		t_a	–	20	–	
Reverse Recovery Stored Charge (Note 4)		t_b	–	17	–	μC
		Q_{RR}	–	0.023	–	

- Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.
- From characterization test data.

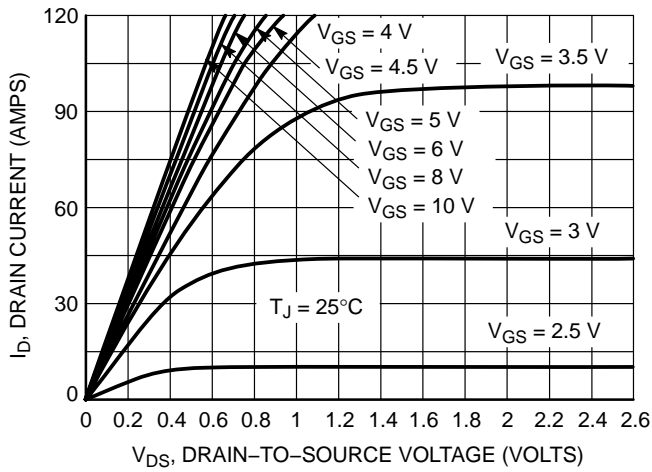


Figure 1. On-Region Characteristics

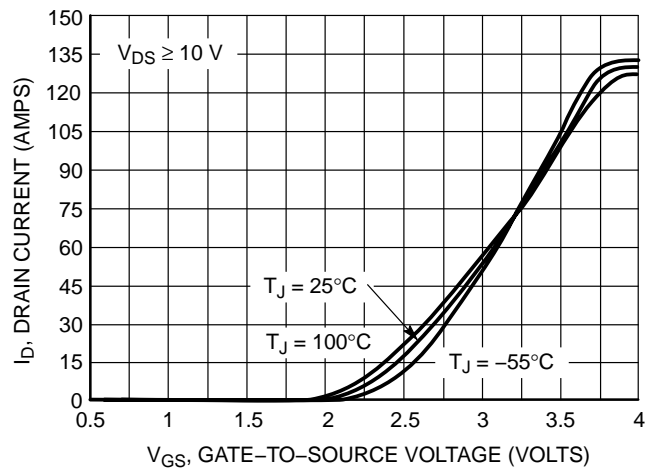


Figure 2. Transfer Characteristics

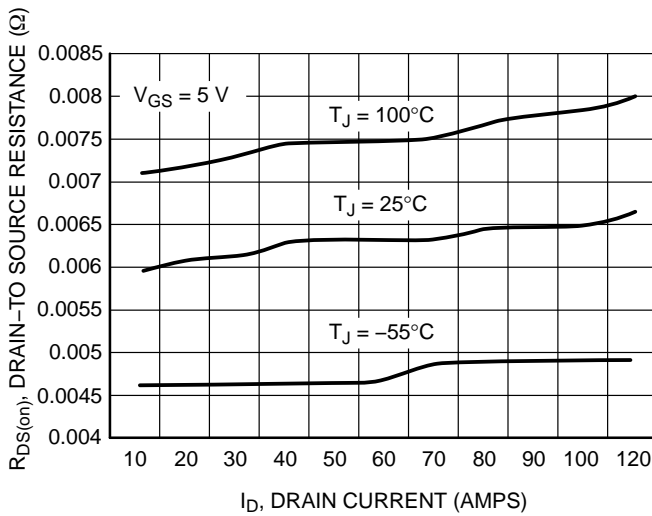


Figure 3. On-Resistance vs. Drain Current and Temperature

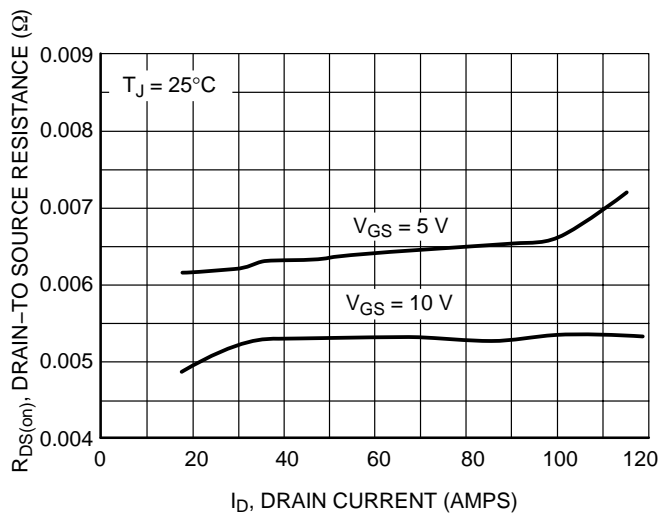


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

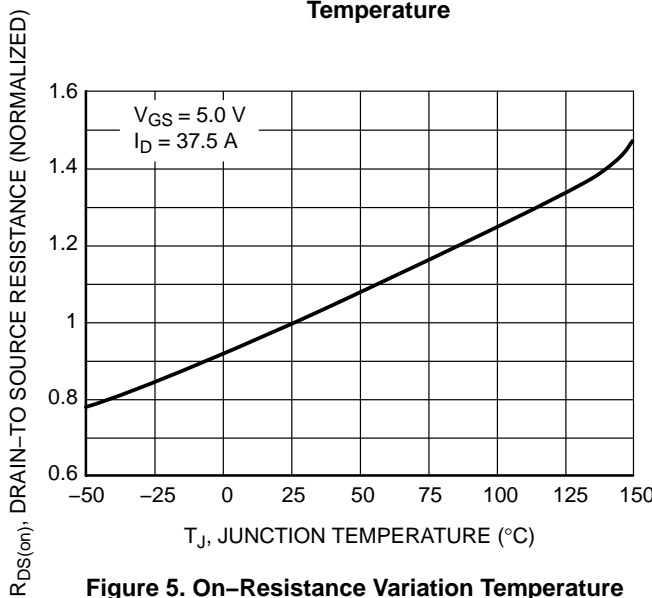


Figure 5. On-Resistance Variation Temperature

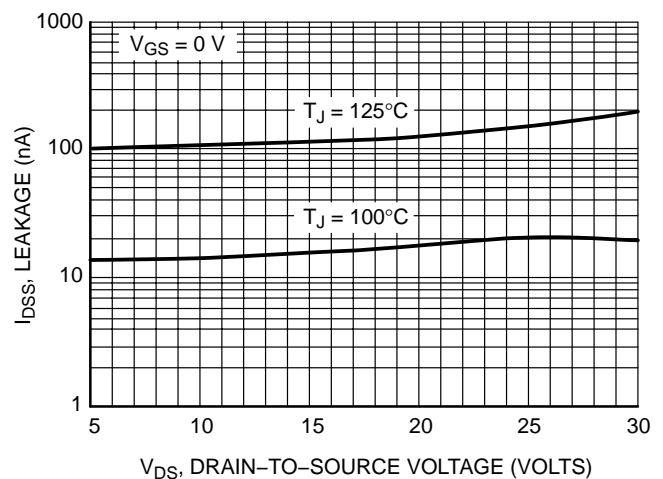


Figure 6. Drain-to-Source Leakage Current vs. Voltage

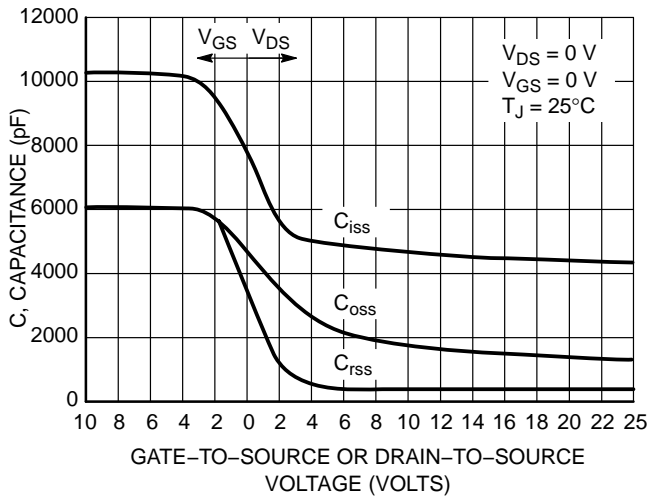


Figure 7. Capacitance Variation

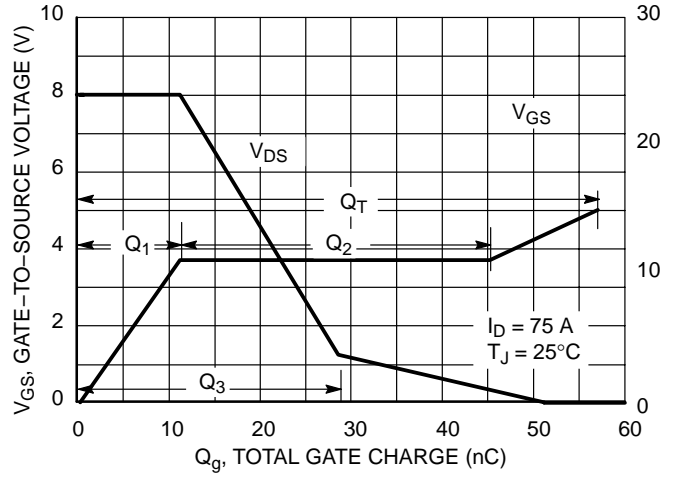


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

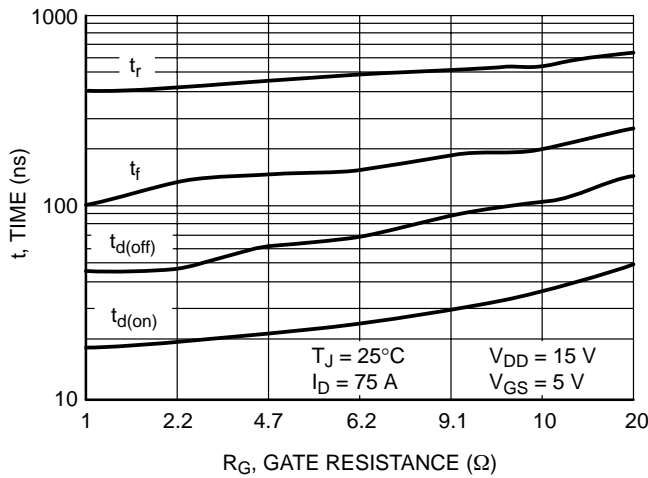


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

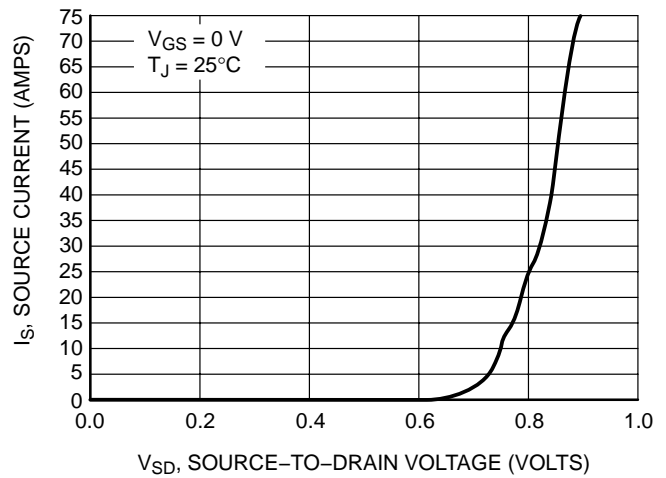


Figure 10. Diode Forward Voltage vs. Current

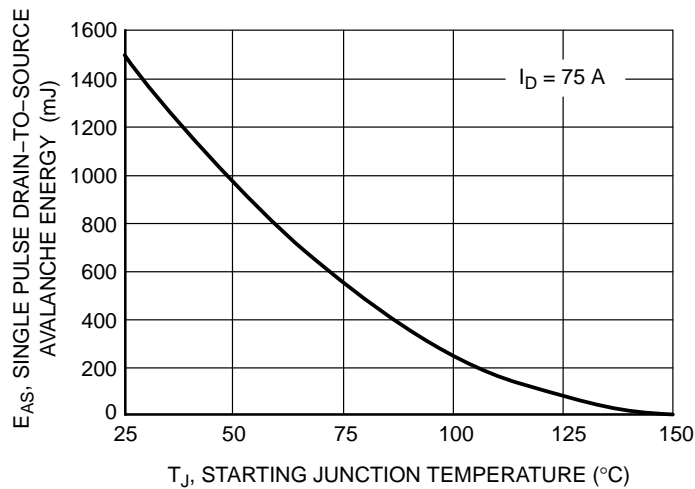
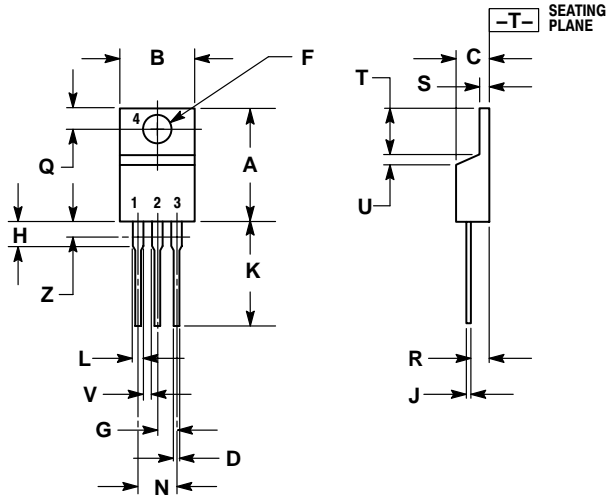


Figure 11. Maximum Avalanche Energy vs. Starting Junction Temperature

NTP75N03L09, NTB75N03L09

PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AA



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

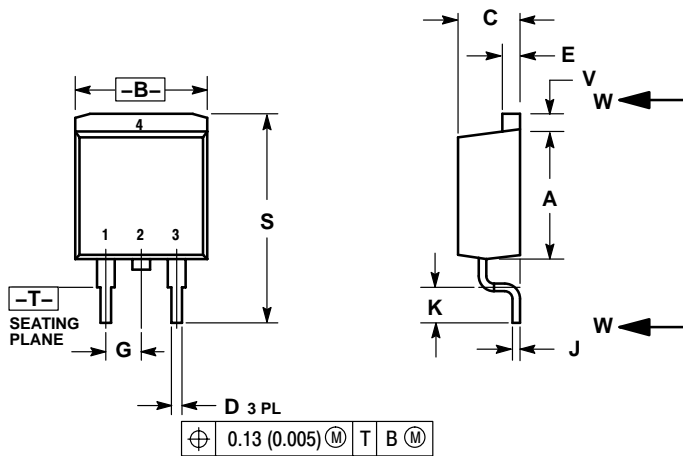
STYLE 5:

- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

NTP75N03L09, NTB75N03L09

PACKAGE DIMENSIONS

D²PAK
CASE 418AA-01
ISSUE O



NOTES:

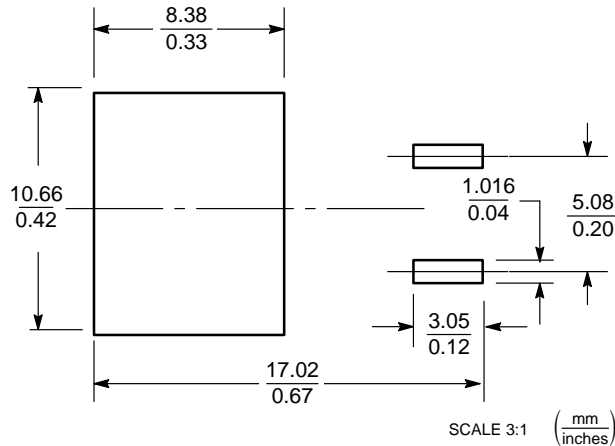
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.036	0.51	0.92
E	0.045	0.055	1.14	1.40
F	0.310	---	7.87	---
G	0.100 BSC		2.54 BSC	
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
M	0.280	---	7.11	---
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

STYLE 2:

- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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